

/ Descriptions

TO-263 N

N-CHANNEL MOSFET in a TO-263 Plastic Package.

/ Features

$V_{DS}=100V$; $I_D=46A$

$R_{DS(on)}@10V \leq 15m\Omega$ (Type.14.8m Ω)

$R_{DS(on)}@4.5V \leq 25m\Omega$ (Type.20.4m Ω)

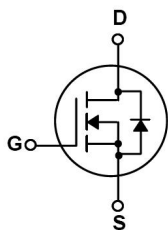
HF Product.

/ Applications

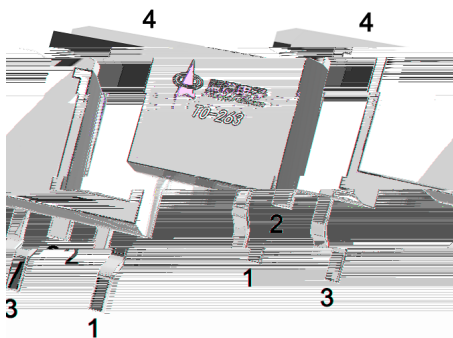
PFC

These devices are well suited for high efficient switched mode power supplies Active power factor correction, electronic lamp ballast based on half bridge topology.

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 4 D

PIN 3 S

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings($T_a=25^\circ\text{C}$)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Continuous Drain Current		I_D	46	A
Pulsed Drain Current		I_{DM}	184	A
Gate-Source Voltage		V_{GS}	± 20	V
Power Dissipation		$P_D(T_c=25^\circ\text{C})$	150	W
Avalanche energy($L=0.5\text{mH}$)		E_{AS}	24.5	mJ
Avalanche Current($L=0.5\text{mH}$)		I_{AS}	7.0	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	
Maximum Junction-to-Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	18	/ W
	Steady-State		48	
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1	

/ Electrical Characteristics($T_a=25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	100	109		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100\text{V}, V_{GS}=0\text{V}$			1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=20\text{A}$		14.8	15	m Ω
		$V_{GS}=4.5\text{V}, I_D=10\text{A}$		20.4	25	
Diode Forward Voltage	V_{SD}	$I_S=1\text{A}, V_{GS}=0\text{V}$			1.2	V
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		1140		pF
Output Capacitance	C_{oss}			600		
Reverse Transfer Capacitance	C_{rss}			60		
Gate resistance	R_g	$V_{GS}=0\text{V}, V_{DS}=0\text{V}$ $f=1\text{MHz}$		1.6		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10\text{V}, V_{DS}=50\text{V},$ $I_D=20\text{A}$		32.5		nC
Total Gate Charge	$Q_{g(4.5V)}$			15.5		
Gate Source Charge	Q_{gs}			6.5		
Gate Drain Charge	Q_{gd}			5		

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=50V$ $R_L=2.5\Omega$ $R_{GEN}=3\Omega$		7		ns
Turn-On Rise Time	t_r			3		
Turn-Off Delay Time	$t_{d(off)}$			27		
Turn-Off Fall Time	t_f			4		

/ Electrical Characteristic Curve

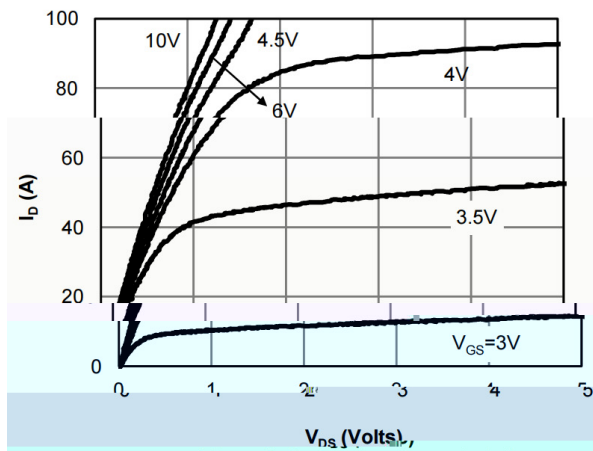


Figure 1: On-Region Characteristics

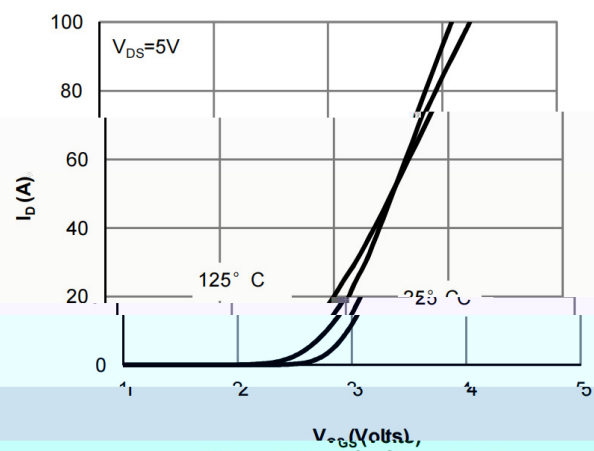


Figure 2: Transfer Characteristics

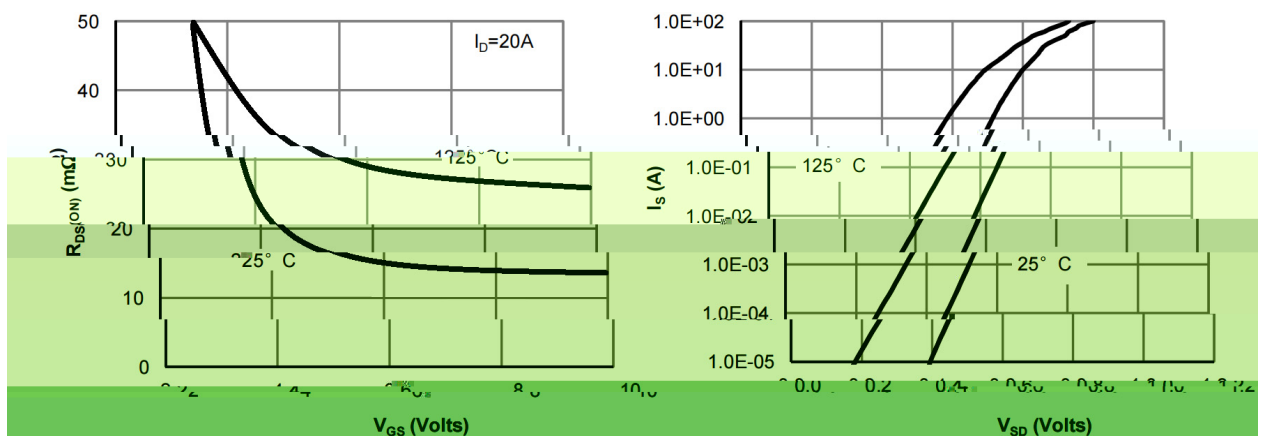
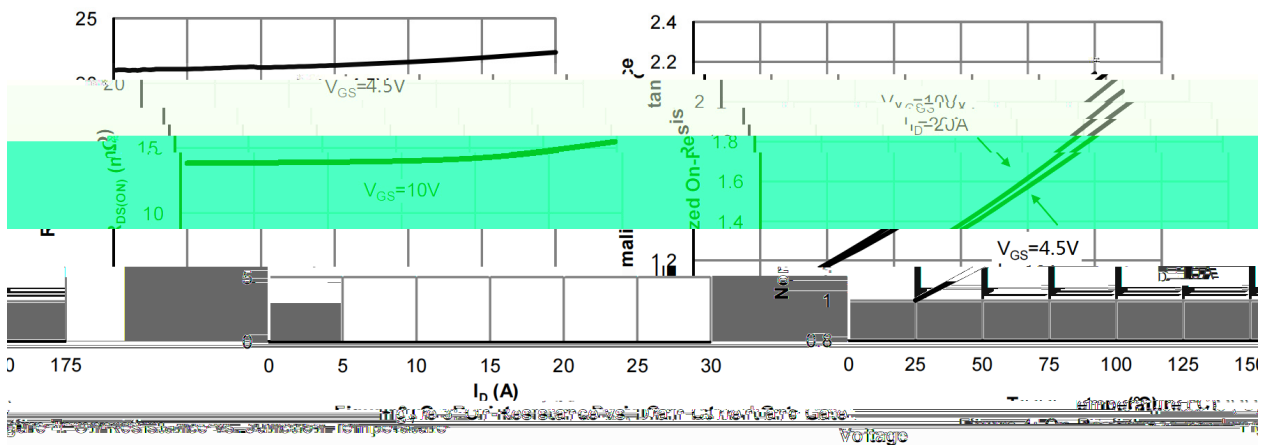
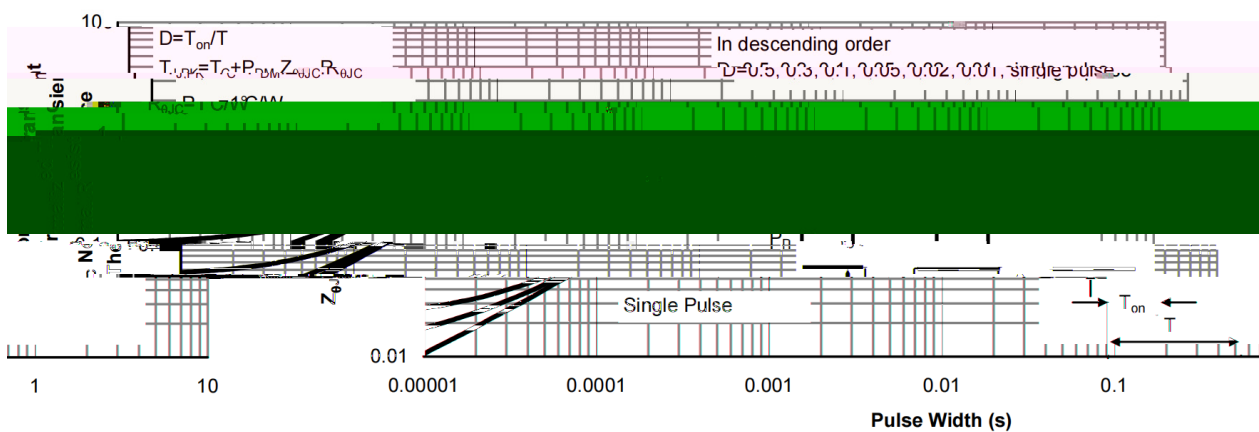
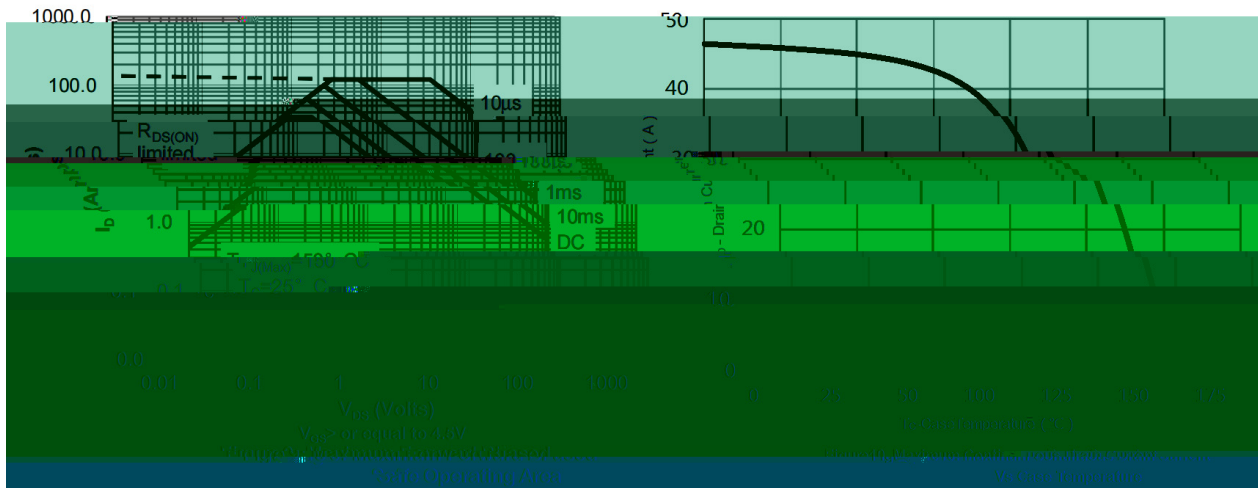
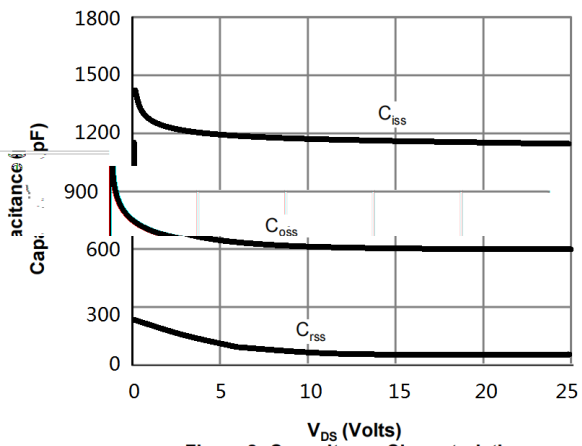
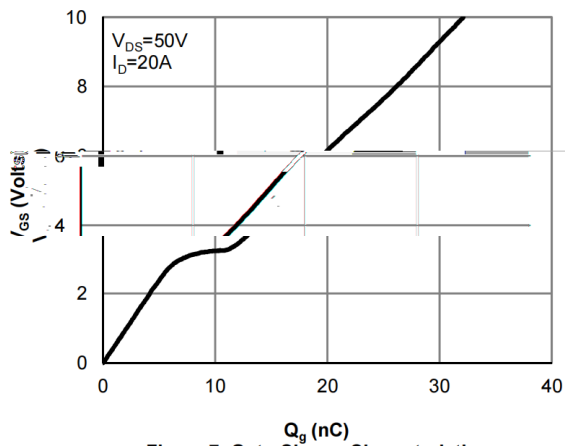


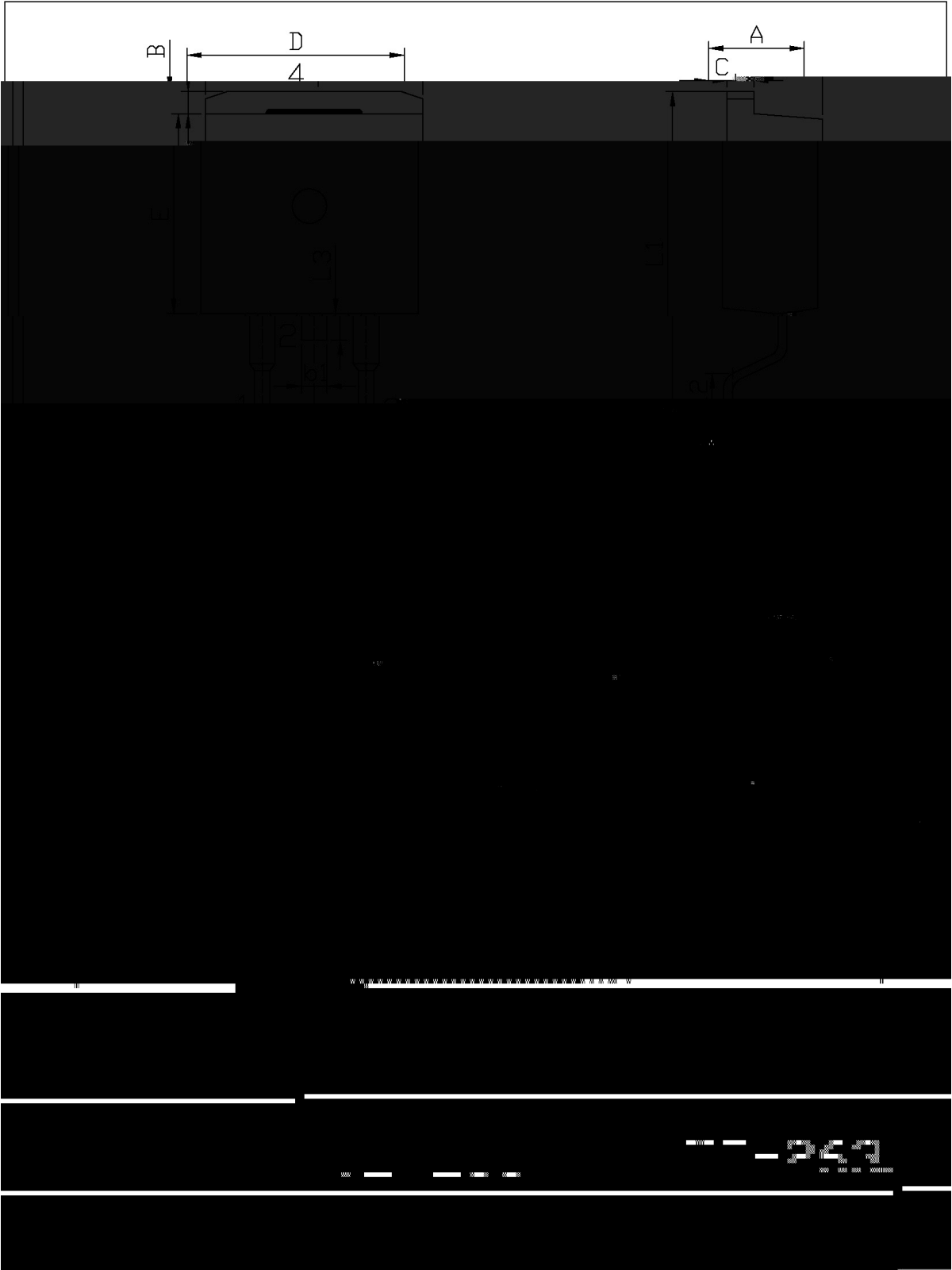
Figure 3: On-Resistance vs. Drain Current

Figure 4: On-Resistance vs. Gate-Source Voltage

/ Electrical Characteristic Curve

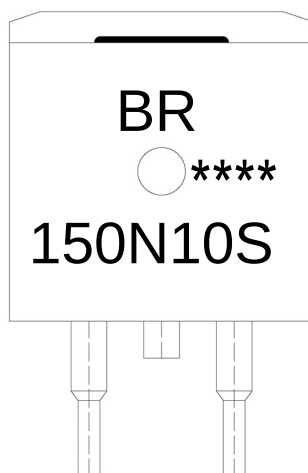


/ Package Dimensions





/ Marking Instructions



BR

150N10S

Note:

BR: Company Code

150N10S: Product Type

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | |
|---|---------|-----------|---|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | 2 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec
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/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
TO-263	800	1	800	6	4,800	13 ×24	360×360×50	380×335×366

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-263	50	20	1,000	5	5,000	532×33×7.0	555×164×50	575×290×180